

Thematic course: Chemical bath synthesis of metal chalcogenide films. Part 29.

Evaluation of formation conditions and synthesis of tin sulfide thin(II) films from solutions using thioacetamide and thiourea

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Abstract

The boundary conditions of formation of SnS and hydroxide including of crystallization factor 298 K were defined by calculation of ions equilibrium using thermodynamic constants in systems “tin chloride – ammonia – thiourea” and “tin chloride – tartaric acid – sodium citrate – thioacetamide”. We demonstrated experimentally the possibility of chemical bath deposition of SnS thin films from these systems. Changes of film microstructure surface depending on temperature and the type of halogenizator were defined with scanning electron microscopy. Energy dispersive microanalysis shows nonstoichiometry of thin films on the sulfur content not exceeding 2.3 at.%.